

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
7 April 2005 (07.04.2005)

PCT

(10) International Publication Number
WO 2005/031842 A3

(51) International Patent Classification⁷: **H01L 21/762**

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(21) International Application Number:
PCT/BE2004/000137

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(22) International Filing Date:
27 September 2004 (27.09.2004)

(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0311347 26 September 2003 (26.09.2003) FR

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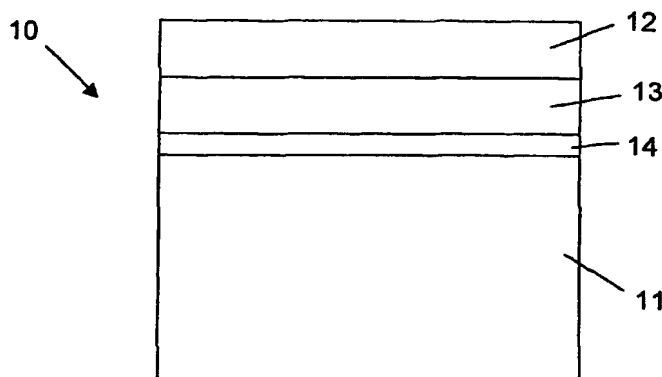
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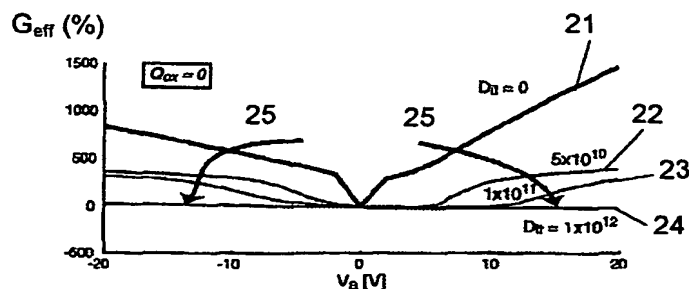
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),

[Continued on next page]

(54) Title: METHOD OF MANUFACTURING A MULTILAYER SEMICONDUCTOR STRUCTURE WITH REDUCED OHMIC
LOSSES



(57) Abstract: The present invention provides a method of manufacturing a multilayer semiconductor structure featuring reduced ohmic losses with respect to standard multilayer semiconductor structures. The semiconductor structure comprises a high resistivity silicon substrate with resistivity higher than 3 K Ω .cm, an active semiconductor layer and an insulating layer in between the silicon substrate and the active semiconductor layer. The method comprises suppressing ohmic losses inside the high resistivity silicon substrate by increasing, with regard to prior art devices, charge trap density between the insulating layer and the silicon substrate. In particular this may be obtained by applying an intermediate layer in between the silicon substrate and the insulating layer, the intermediate layer comprising grains having a size, wherein the mean size of the grains of the intermediate layer is smaller than 150 nm, preferably smaller than 50 nm.





European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

Declaration under Rule 4.17:

— *of inventorship (Rule 4.17(iv)) for US only*

(88) Date of publication of the international search report:

12 May 2005

Published:

— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.